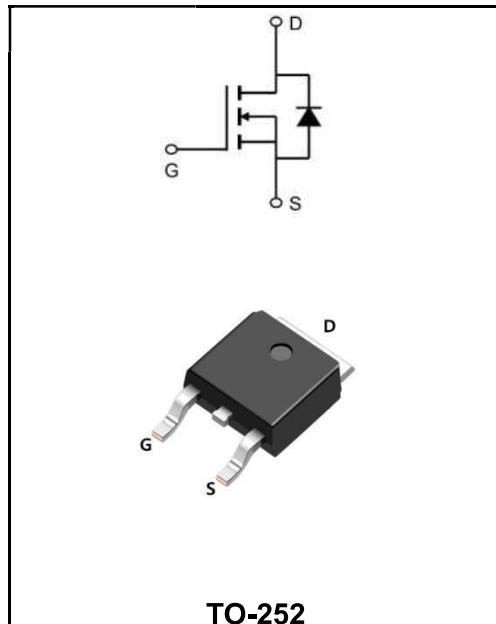


300V N-CHANNEL ENHANCEMENT MODE MOSFET
MAIN CHARACTERISTICS

I_D	5A
V_{DSS}	300V
R_{DSON-typ(@V_{GS}=10V)}	< 1.5Ω(Type:1.2Ω)


Application

- ◆ Eliminate stroboscopic
- ◆ Brush motor

Product Specification Classification

Part Number	Package	Marking	Pack
YFW5N30AD	TO-252	YFW 5N30AD XXXXX	2500PCS/Tape

Maximum Ratings at T_c=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage (V _{GS} = 0V)	V _{DS}	300	V
Continuous Drain Current	I _D	5	A
Pulsed Drain Current	I _{DM}	20	A
Gate - Source Voltage	V _{GS}	±25	V
Single Pulse Avalanche Energy	E _{AS}	50	mJ
Avalanche Current	I _{AR}	3.2	A
Repetitive Avalanche Energy	E _{AR}	1.5	mJ
Power Dissipation(T _A =25°C)	P _D	58.7	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C
Thermal Resistance, Junction-to-case	R _{θJC}	2.13	°C/W
Thermal Resistance, Junction ambient	R _{θJA}	60	°C/W

Maximum Ratings at T_c=25°C unless otherwise specified

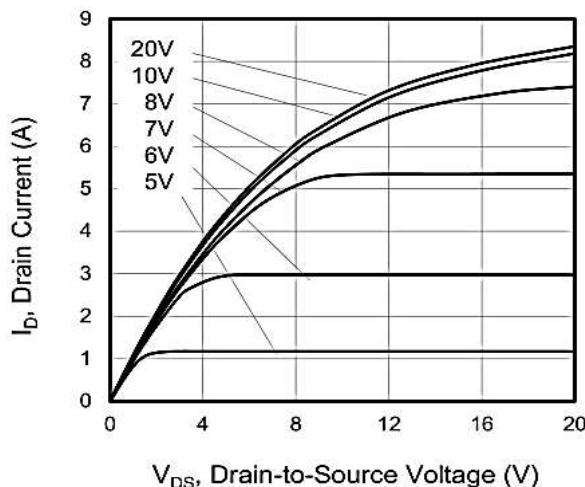
Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	V(BR)DSS	300	330	-	V
Zero Gate Voltage Drain Current	V _{DS} =300V, V _{GS} =0V, T _J =25°C	I _{DSS}	-	-	1	μA
	V _{DS} =240V, V _{GS} =0V, T _J =125°C		-	-	100	
Gate-Source Leakage	V _{GS} =±25V	I _{GSS}	-	-	±100	nA
Gate- Source Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	V _{GS(th)}	2.0	3.5	4.0	V
Drain-Source On-Resistance	V _{GS} =10V, I _D =2.5A	R _{DS(ON)}	-	1.2	1.5	Ω
Input Capacitance	V _{DS} =25V V _{GS} =0V f=1MHz	C _{iss}	-	291	-	pF
Output Capacitance		C _{oss}	-	43	-	
Reverse Transfer Capacitance		C _{rss}	-	7	-	
Total Gate Charge	V _{DD} =240V I _D =5A V _{GS} =10V	Q _g	-	8.4	-	nC
Gate-Source Charge		Q _{gs}	-	1.2	-	
Gate-Drain Charge		Q _{gd}	-	3.3	-	
Turn-on delay time	V _{DD} =150V I _D =5A R _G =25Ω	t _{d(on)}	-	20	-	nS
Turn-on Rise Time		T _r	-	50	-	
Turn-Off Delay Time		t _{d(OFF)}	-	70	-	
Turn-Off Fall Time		t _f	-	53	-	
Continuous Body Diode Current	T _c =25°C	I _s	-	-	5	A
Pulsed Diode Forward Current		I _{SM}	-	-	20	
Body Diode Voltage	T _J = 25°C, I _{SD} = 5A, V _{GS} = 0V	V _{SD}	-	-	1.4	V
Reverse Recovery Time	V _{GS} = 0V, I _s = 5A diF/dt =100A /μs	t _{rr}	-	263	-	nS
Reverse Recovery Charge		Q _{rr}	-	1.9	-	uC

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The EAS data shows Max. rating . IAS = 3.2A, VDD = 50V, RG = 25 Ω, Starting TJ = 25 °C
- 3、The test condition is Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

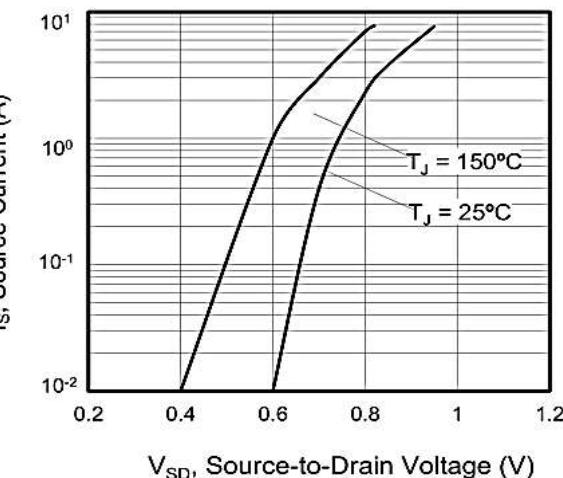
Ratings and Characteristic Curves

Typical Characteristics



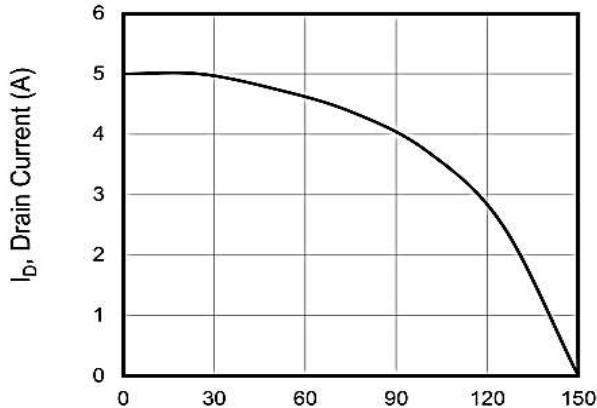
V_{DS}, Drain-to-Source Voltage (V)

Figure 1. Output Characteristics (T_J = 25°C)



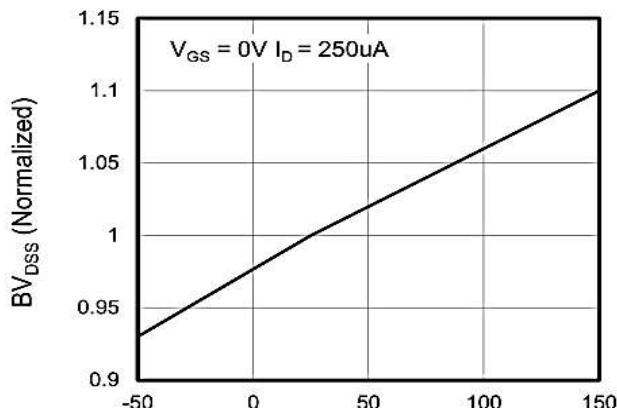
V_{SD}, Source-to-Drain Voltage (V)

Figure 2. Body Diode Forward Voltage



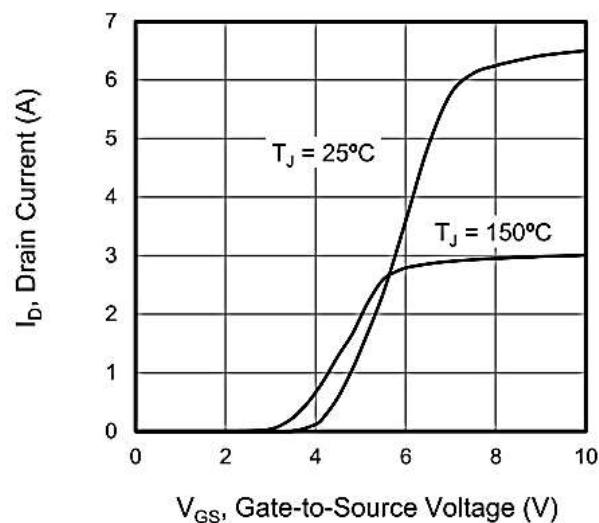
T_C, Case Temperature (A)

Figure 3. Drain Current vs. Temperature



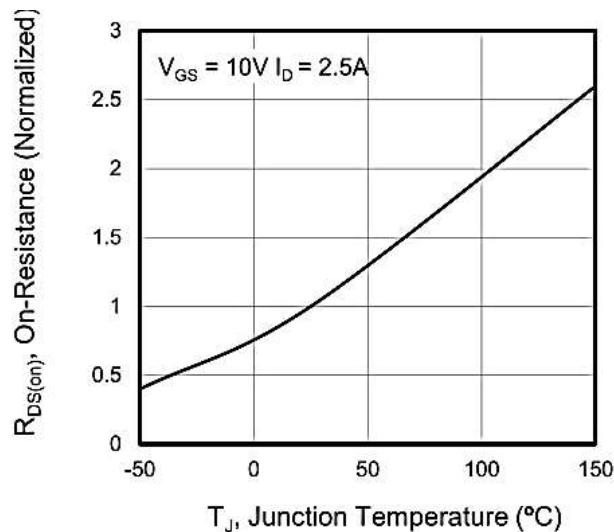
T_J, Junction Temperature (°C)

Figure 4. BV DSS Variation vs. Temperature



V_{GS}, Gate-to-Source Voltage (V)

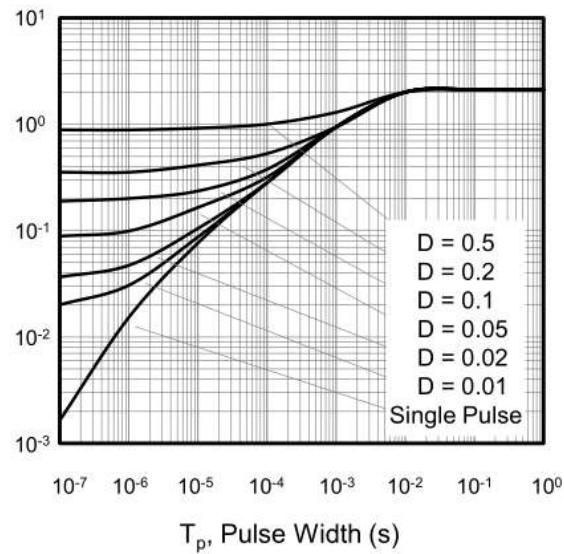
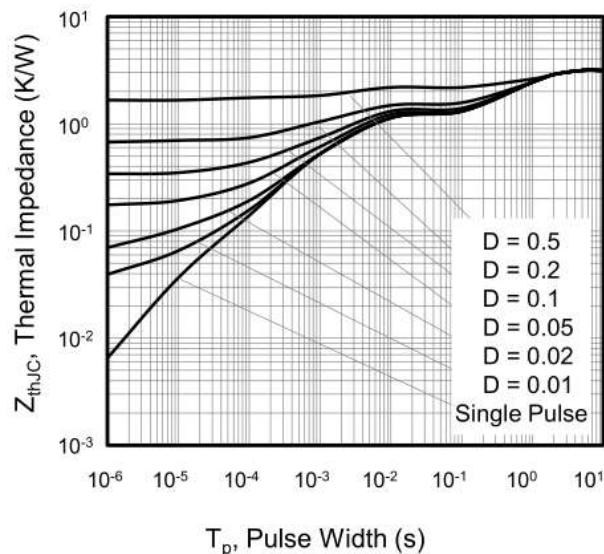
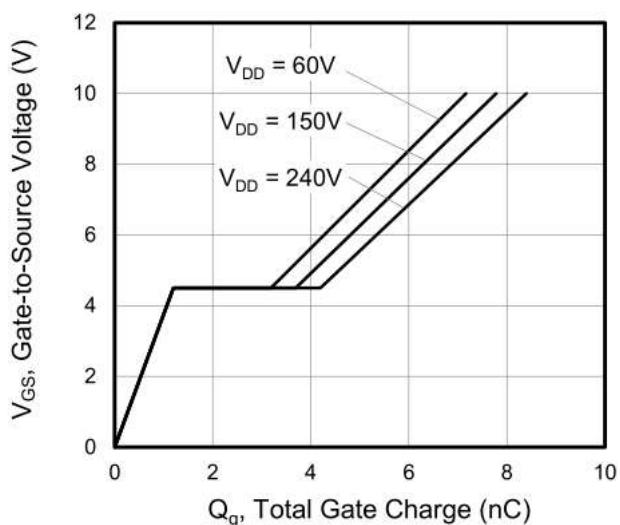
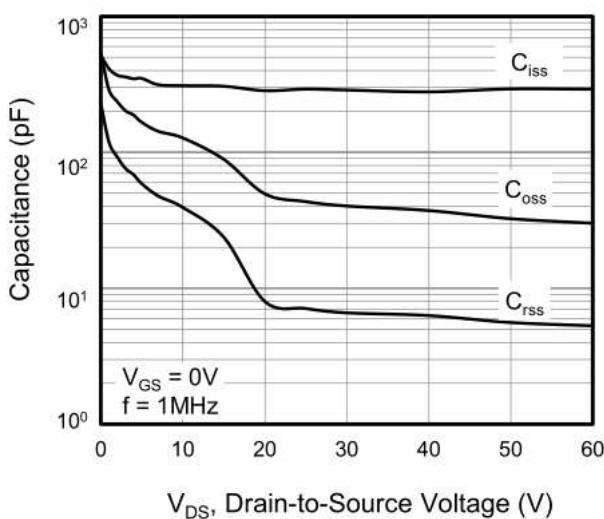
Figure 5. Transfer Characteristics



T_J, Junction Temperature (°C)

Figure 6. On-Resistance vs. Temperature

Ratings and Characteristic Curves



Package Outline Dimensions Millimeters

TO-252

Dim.	Min.	Typ.	Max.
A	2.10	-	2.50
A2	0	-	0.10
B	0.66	-	0.86
B2	5.18	-	5.48
C	0.40	-	0.60
C2	0.44	-	0.58
D	5.90	-	6.30
D1	5.30REF		
E	6.40	-	6.80
E1	4.63	-	-
G	4.47	-	4.67
H	9.50	-	10.70
L	1.09	-	1.21
L2	1.35	-	1.65
V1	-	7°	-
V2	0°	-	6°

All Dimensions in millimeter